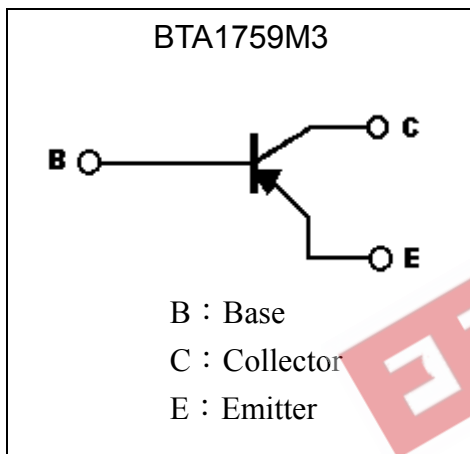
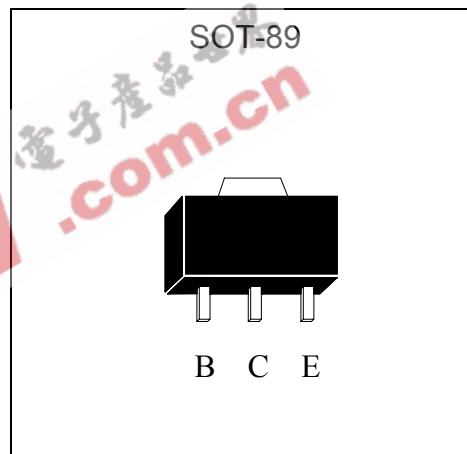


**High Voltage PNP Epitaxial Planar Transistor**

# BTA1759M3

**Description**

- High breakdown voltage. ( $BV_{CEO} = -400V$ )
- Low saturation voltage, typically  $V_{CE(sat)} = -0.07V$  at  $I_C/I_B = -10mA/-1mA$ .
- Wide SOA (safe operation area).
- Complementary to BTA4505M3.

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a = 25^\circ C$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	-400	V
Collector-Emitter Voltage	$V_{CEO}$	-400	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-300	mA
Power Dissipation	$P_d$	0.6	W
		1 (Note 1)	W
		2 (Note 2)	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	208	$^\circ C/W$
		125 (Note 1)	$^\circ C/W$
		62.5 (Note 2)	$^\circ C/W$
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ C$

Note : 1. When mounted on FR-4 PCB with area measuring  $10 \times 10 \times 1$  mm  
 2. When mounted on ceramic with area measuring  $40 \times 40 \times 1$  mm

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-400	-	-	V	I <sub>C</sub> =-50μA
BV <sub>CEO</sub>	-400	-	-	V	I <sub>C</sub> =-1mA
BV <sub>EBO</sub>	-6	-	-	V	I <sub>E</sub> =-50μA
I <sub>CBO</sub>	-	-	-10	μA	V <sub>CB</sub> =-400V
I <sub>EBO</sub>	-	-	-10	μA	V <sub>EB</sub> =-6V
I <sub>CES</sub>	-	-	-10	μA	V <sub>CB</sub> =-400V
V <sub>CE(sat)</sub> 1	-	-	-0.2	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =-0.1mA
*V <sub>CE(sat)</sub> 2	-	-	-0.3	V	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA
*V <sub>CE(sat)</sub> 3	-	-	-0.6	V	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA
*V <sub>BE(sat)</sub>	-	-	-0.9	V	I <sub>C</sub> =-20mA, I <sub>B</sub> =-2mA
h <sub>FE</sub> 1	50	-	-	-	V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA
*h <sub>FE</sub> 2	56	-	270	-	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA
*h <sub>FE</sub> 3	50	-	-	-	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA
*h <sub>FE</sub> 4	40	-	-	-	V <sub>CE</sub> =-10V, I <sub>C</sub> =-100mA
C <sub>ob</sub>	-	-	6	pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0A, f=1MHz

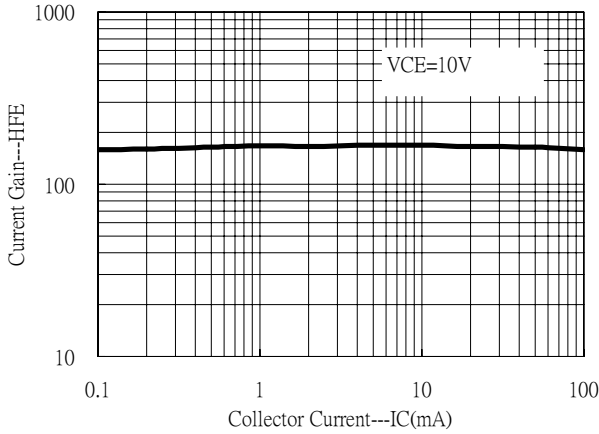
\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE</sub>**

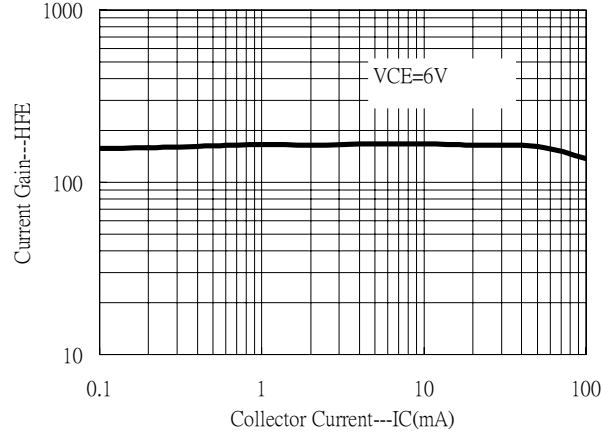
Rank	K	P	Q
Range	56~120	82~180	120~270

**Characteristic Curves**

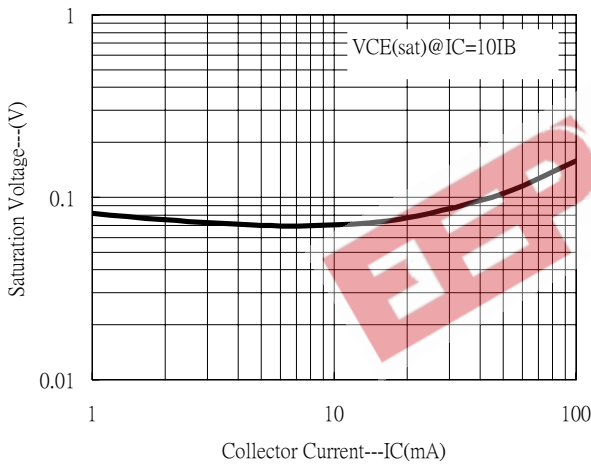
Current Gain vs Collector Current



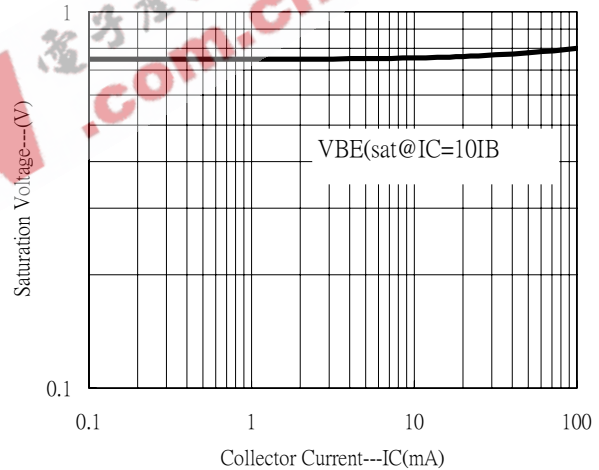
Current Gain vs Collector Current



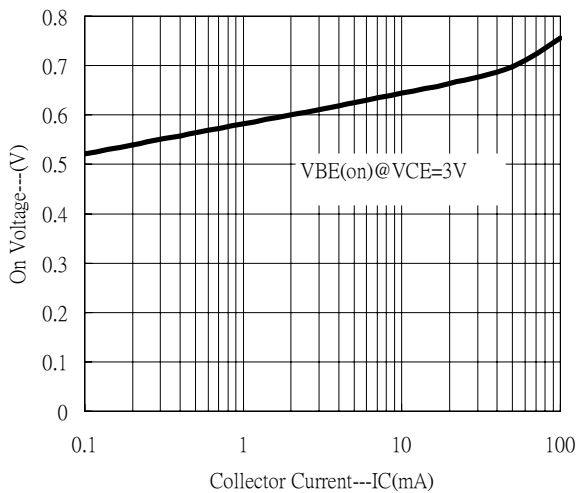
Saturation Voltage vs Collector Current



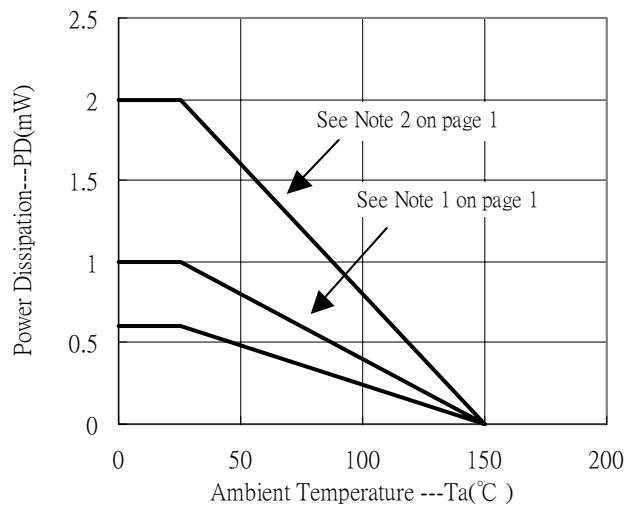
Saturation Voltage vs Collector Current



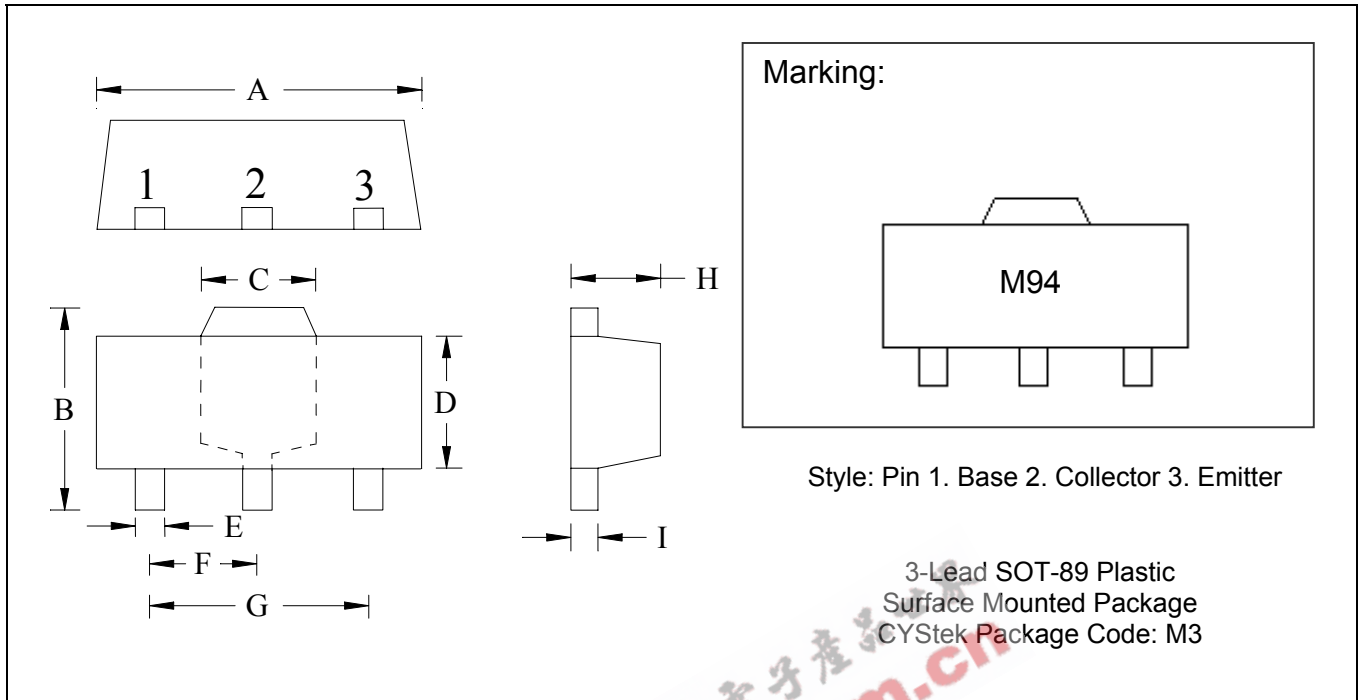
On Voltage vs Collector Current



Power Derating Curves



**SOT-89 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1732	0.1811	4.40	4.60	F	0.0583	0.0598	1.48	1.527
B	0.1594	0.1673	4.05	4.25	G	0.1165	0.1197	2.96	3.04
C	0.0591	0.0663	1.50	1.70	H	0.0551	0.0630	1.40	1.60
D	0.0945	0.1024	2.40	2.60	I	0.0138	0.0161	0.35	0.41
E	0.01417	0.0201	0.36	0.51					

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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